

Features

- Trench Power LV MOSFET Technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed Switching
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings

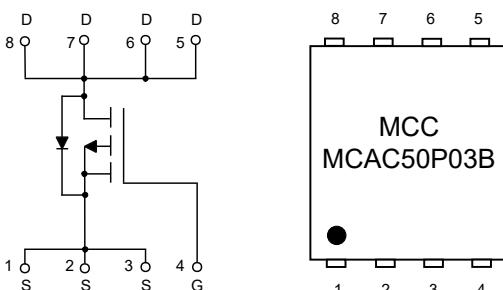
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 17°C/W Junction to Ambient (Note 2)
- Thermal Resistance: 1.5°C/W Junction to Case

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 25	V
Continuous Drain Current $T_C=25^\circ\text{C}$	I_D	-50	A
$T_C=100^\circ\text{C}$	I_D	-32	
Pulsed Drain Current (Note 3)	I_{DM}	-200	A
Total Power Dissipation (Note 4)	P_D	83	W
Single Pulsed Avalanche Energy (Note 5)	E_{AS}	360	mJ

Note:

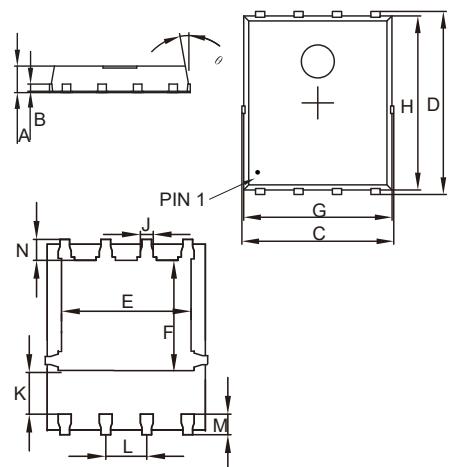
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R_{GJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-case thermal resistance.
5. $T_J=25^\circ\text{C}$, $V_{DD}=-25\text{V}$, $V_G=-10\text{V}$, $L=2\text{mH}$.

Internal Structure and Marking Code



P-CHANNEL MOSFET

DFN5060



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.031	0.047	0.80	1.20	
B	0.010		0.254		TYP.
C	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
E	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
H	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
M	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate-Source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 25V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.2	-1.8	-2.8	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-20A$		4	5.5	$m\Omega$
		$V_{GS}=-4.5V, I_D=-20A$		6	9.5	
Gate Resistance	R_g	f=1Mhz, Drain open		6.5		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				-50	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-20A$			-1.2	V
Reverse Recovery Time	t_{rr}	$I_S=-15A, di/dt=100A/\mu s$		24		ns
Reverse Recovery Charge	Q_{rr}			8.5		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$		6426		pF
Output Capacitance	C_{oss}			754		
Reverse Transfer Capacitance	C_{rss}			670		
Total Gate Charge	Q_g	$V_{DS}=-15V, V_{GS}=-10V, I_D=-20A$		111		nC
Gate-Source Charge	Q_{gs}			16		
Gate-Drain Charge	Q_{gd}			22.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-15V, V_{GS}=-10V, R_G=3\Omega, I_D=-20A$		13.6		ns
Turn-On Rise Time	t_r			25.7		
Turn-Off Delay Time	$t_{d(off)}$			192		
Turn-Off Fall Time	t_f			90		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

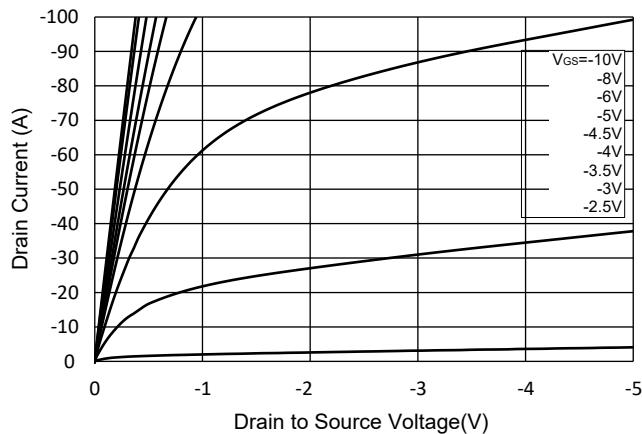


Fig.2 Transfer Characteristic

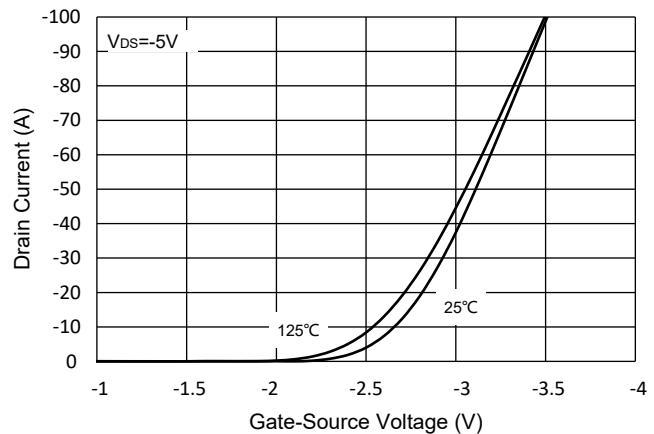


Fig.3 R_{D5(ON)}-V_{gs}

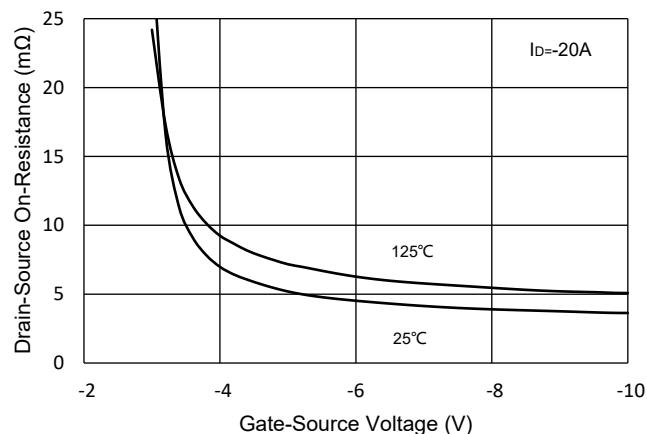


Fig.4 R_{D5(ON)}-I_D

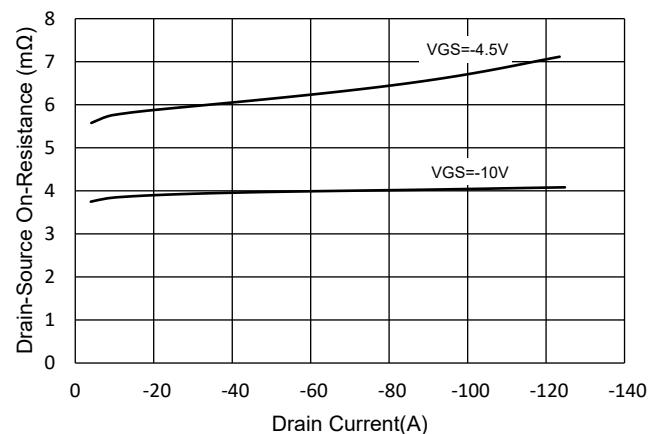


Fig.5 Capacitance Characteristics

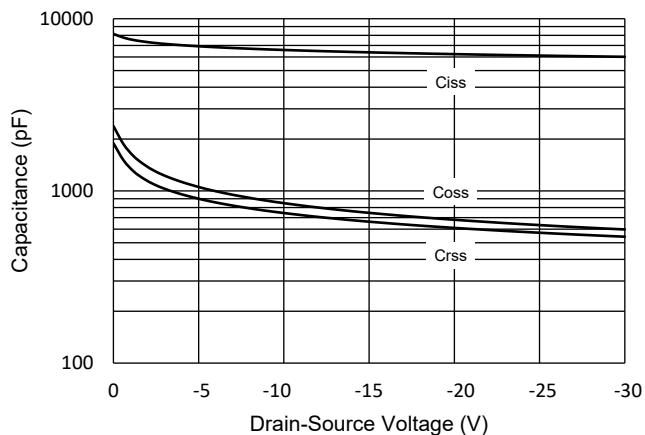
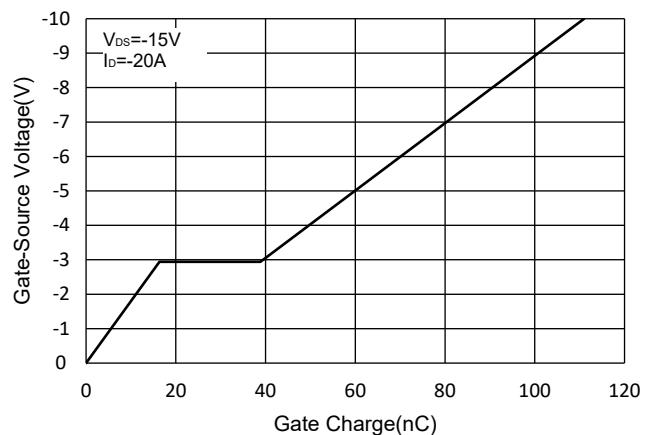


Fig.6 Gate Charge



Curve Characteristics

Fig.7 Normalized Threshold Voltage

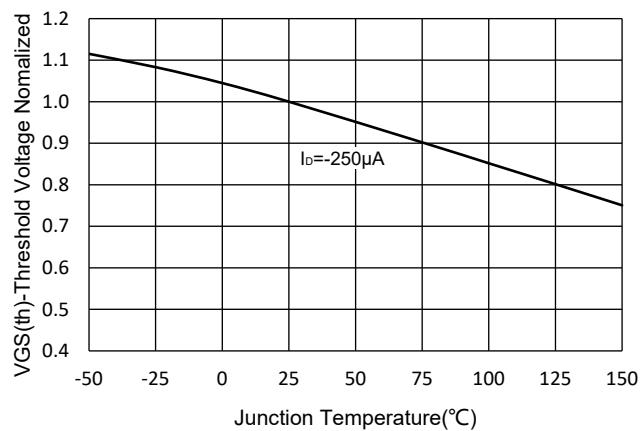


Fig.8 Normalized On Resistance Characteristics

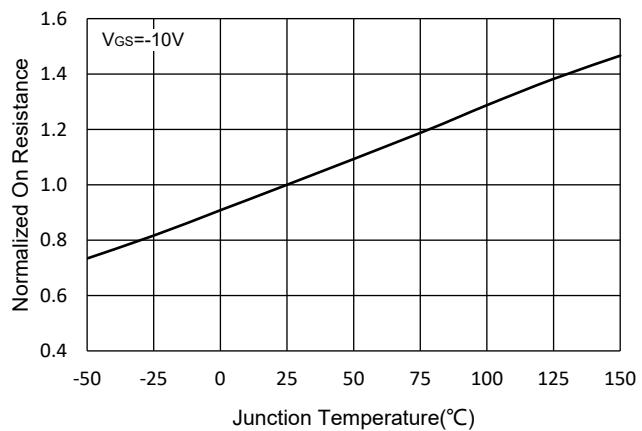


Fig.9 IS-VSD

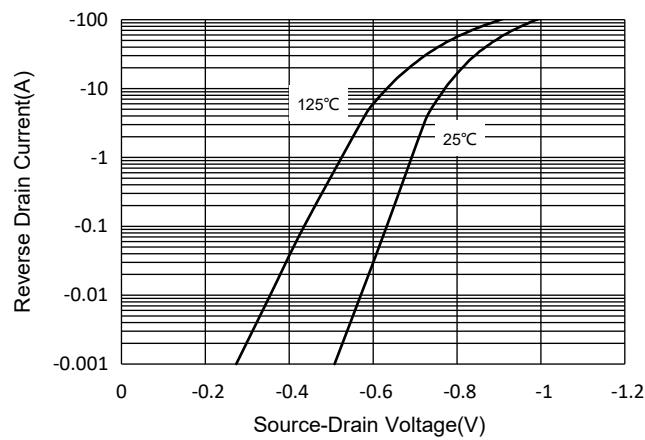


Fig.10 Drain Current

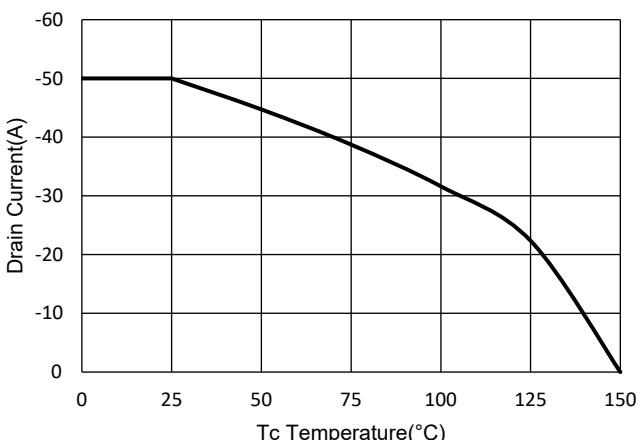
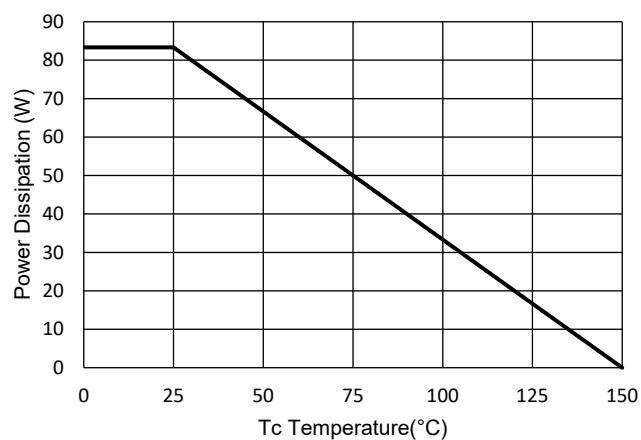


Fig.11 Power Dissipation



Curve Characteristics

Fig.12 Safe Operation Area

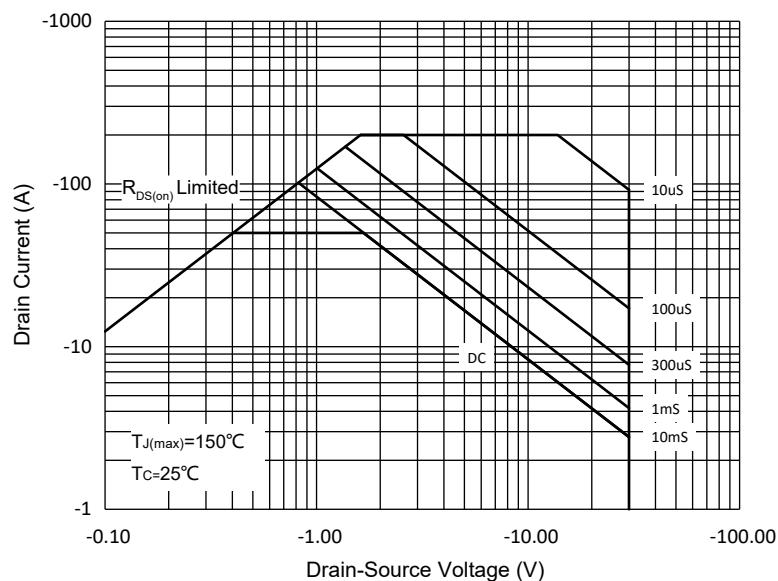
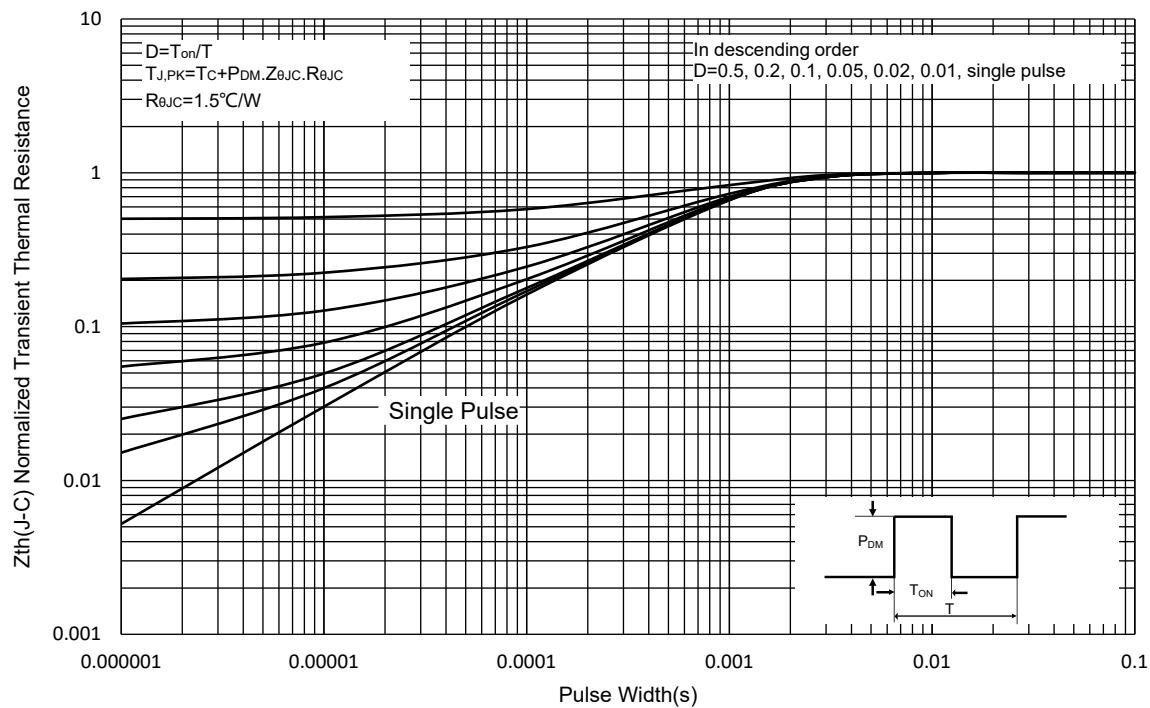


Fig.13 Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 5Kpcs/Reel

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